TOSHIBA CCD LINEAR IMAGE SENSOR   CCD (Charge Coupled Device)

TCD1209DG

The TCD1209DG is a high speed and low dark current 2048 elements CCD image sensor.

The sensor is designed for facsimile, imagescanner and OCR. The device contains a row of 2048 elements photodiodes which provide a 8 lines / mm (200 DPI) across a B4 size paper. The device is operated by 5 V (pulse), and 12 V power supply.

FEATURES

- Number of Image Sensing Elements : 2048 elements
- Image Sensing Element Size
    : 14 µm by 14 µm on 14 µm centers
- Photo Sensing Region   : High sensitive and low voltage dark signal pn photodiode
- Clock   : 2 phase (5 V)
- Package   : 22pin Cerdip

WDIP22-G-400-2.54A (A)

MAXIMUM RATINGS (Note 1)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Clock Pulse Voltage	V_φ	−0.3~8	V
Shift Pulse Voltage	V_{SH}		
Reset Pulse Voltage	V_{RS}		
Clamp Pulse Voltage	V_{CP}		
Power Supply Voltage	V_{OD}	−0.3~15	
Operating Temperature	T_{opr}	−25~60	℃
Storage Temperature	T_{stg}	−40~100	℃

Note 1: All voltage are with respect to SS terminals (Ground).

PIN CONNECTION

Left	Pin		Pin	Right
OS	1		22	SH
SS	2		21	CP
OD	3		20	NC
NC	4		19	NC
$\varphi 1$	5		18	RS
$\varphi 2$	6		17	$\varphi 2B$
NC	7		16	NC
NC	8		15	NC
NC	9		14	NC
NC	10		13	NC
NC	11		12	NC

(inside markings: 1, 2048)

(TOP VIEW)
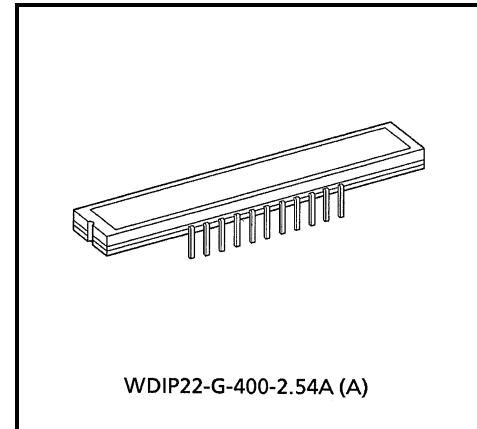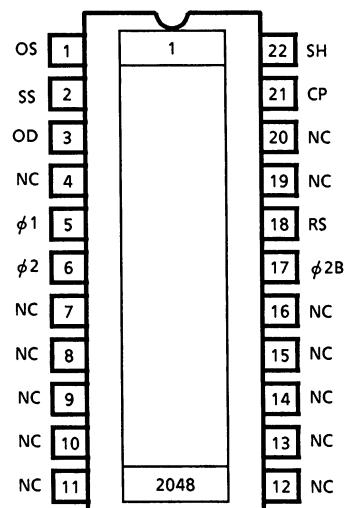
CIRCUIT DIAGRAM
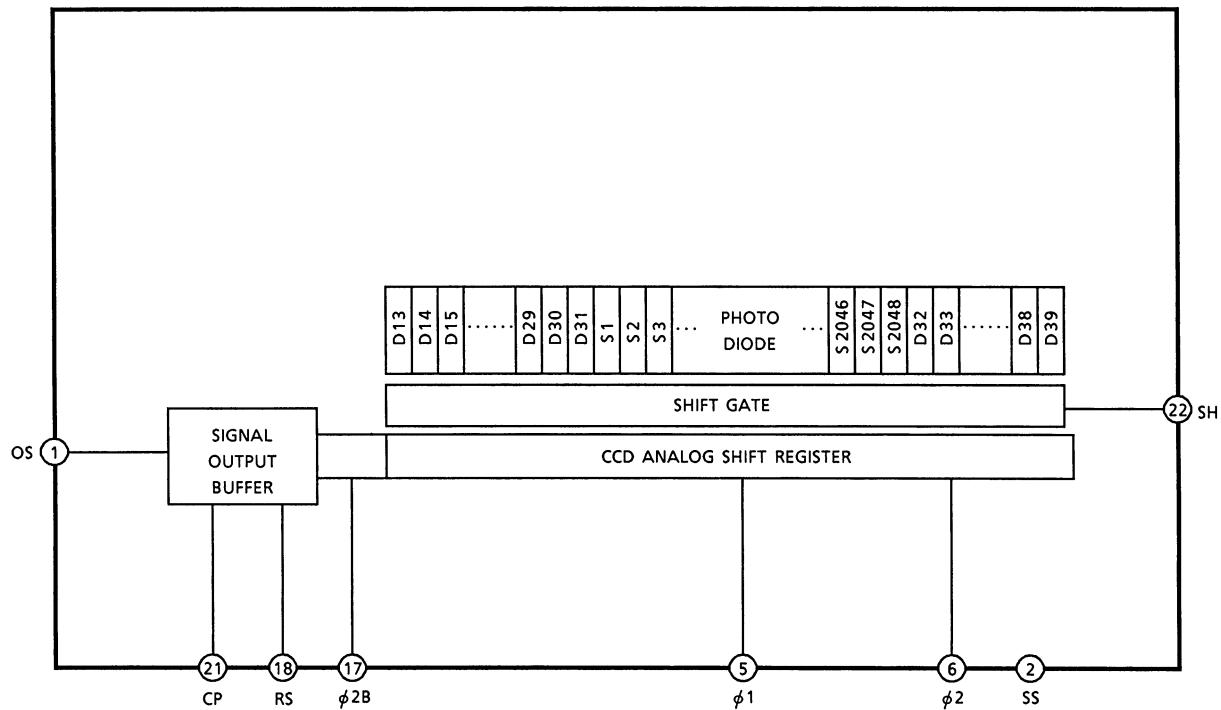
PIN NAMES

φ1	Clock (Phase 1)
φ2	Clock (Phase 2)
φ2B	Final Stage Clock (Phase 2)
SH	Shift Gate
RS	Reset Gate
CP	Clamp Gate
OS	Signal Output
OD	Power
SS	Ground
NC	Non Connection

OPTICAL / ELECTRICAL CHARACTERISTICS

(Ta = 25°C, V_{OD} = 12V, V_φ = V_{SH} = V_{RS} = V_{CP} = 5V (PULSE), f_φ = 1MHz, t_{INT} (INTEGRATION TIME) = 10ms, LIGHT SOURCE = DAYLIGHT FLUORESCENT LAMP, LOAD RESISTANCE = 100 kΩ)

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT	NOTE
Sensitivity	R	25	31	37	V / (lx·s)	
Photo Response Non Uniformity	PRNU	—	3	10	%	(Note 2)
	PRNU (3)	—	4	10	mV	(Note 8)
Saturation Output Voltage	V_{SAT}	1.5	2.0	—	V	(Note 3)
Saturation Exposure	SE	0.04	0.06	—	lx·s	(Note 4)
Dark Signal Voltage	V_{DRK}	—	1.0	2.5	mV	(Note 5)
Dark Signal Non Uniformity	DSNU	—	1.0	2.5	mV	(Note 5)
DC Power Dissipation	P_D	—	160	400	mW	
Total Transfer Efficiency	TTE	92	98	—	%	
Output Impedance	Z_o	—	0.2	1	kΩ	
Dynami Range	DR	—	2000	—	—	(Note 6)
DC Signal Output Voltage	V_{OS}	4.0	5.5	7.0	V	(Note 7)
Random Noise	$N_{D\sigma}$	—	0.6	—	mV	(Note 9)

Note 2: Measured at 50% of SE (Typ.)

Definition of PRNU : $PRNU = \frac{\Delta\chi}{\bar{\chi}} \times 100 (\%)$

Where $\bar{\chi}$ is average of total signal outputs and $\Delta\chi$ is maximum deviation from $\bar{\chi}$ under uniform illumination.

Note 3: V_{SAT} is defined as minimum saturation output voltage of all effective pixels.

Note 4: Definition of SE : $SE = \frac{V_{SAT}}{R} (lx \cdot s)$

Note 5: V_{DRK} is defined as average dark signal voltage of all effective pixels.
DSNU is defined as different voltage between V_{DRK} and V_{MDK} when V_{MDK} is maximum dark signal voltage.
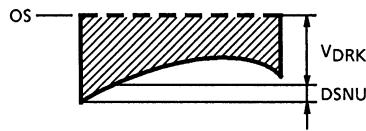

Note 6: Definition of DR : $DR = \dfrac{V_{SAT}}{V_{DRK}}$

V_{DRK} is proportional to t_{INT} (Integration Time).
So the shorter t_{INT} condition makes wider DR values.

Note 7: DC signal output voltage and DC compensation output voltage are defined as follows:
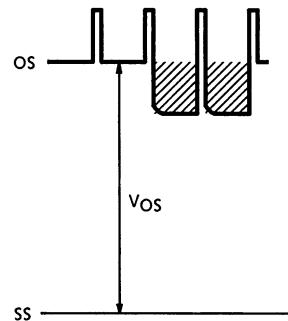
Note 8: PRNU (3) is defined as maximum voltage with next pixel, where measured 5% of SE (Typ.)

Note 9: Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.
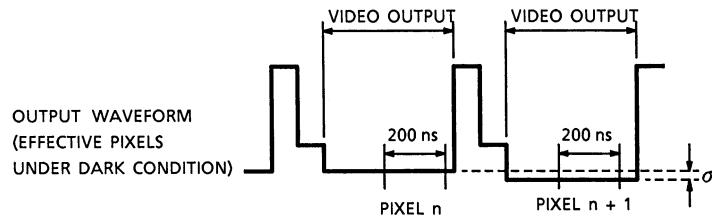
1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
2) Each of the output levels at video output periods averaged over 200 nanosecond period to get Vn and Vn + 1.
3) Vn + 1 is subtracted from Vn to get. ΔV.

$$\Delta V = Vn - Vn+1$$

4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30}\sum_{i=1}^{30}\left|\Delta V^i\right| \qquad \sigma = \sqrt{\frac{1}{30}\sum_{i=1}^{30}\left(\left|\Delta Vi\right| - \overline{\Delta V}\right)^2}$$

5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10}\sum_{j=1}^{10}\sigma j$$

6) σ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as follows.

$$\text{Random noise} = \frac{1}{\sqrt{2}}\overline{\sigma}$$

OPERATING CONDITION

CHARACTERISTIC		SYMBOL	MIN	TYP.	MAX	UNIT
Clock Pulse Voltage	"H" Level	$V_\varphi 1$	4.5	5	5.5	V
	"L" Level	$V_\varphi 2$	0	—	0.5	
Final Stage Clock Voltage	"H" Level	$V_\varphi 2B$	4.5	5	5.5	V
	"L" Level		0	—	0.5	
Shift Pulse Voltage	"H" Level	V_{SH}	4.5	5	5.5	V
	"L" Level		0	—	0.5	
Reset Pulse Voltage	"H" Level	V_{RS}	4.5	5	5.5	V
	"L" Level		0	—	0.5	
Clamp Pulse Voltage	"H" Level	V_{CP}	4.5	5	5.5	V
	"L" Level		0	—	0.5	
Power Supply Voltage		V_{OD}	11.4	12.0	13.0	V

CLOCK CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	MIN	TYP.	MAX	UNIT
Clock Pulse Frequency		f_φ	—	1	20	MHz
Reset Pulse Frequency		f_{RS}	—	1	20	MHz
Clock Capacitance	(Note 10)	$C_\varphi 1$	—	200	—	pF
		$C_\varphi 2$	—	200	—	
Final Stage Clock Capacitance		$C_\varphi B$	—	10	20	pF
Shift Gate Capacitance		C_{SH}	—	30	—	pF
Reset Gate Capacitance		C_{RS}	—	10	20	pF
Clamp Gate Capacitance		C_{CP}	—	10	20	pF

Note 10:   VOD = 12 V

TIMING CHART
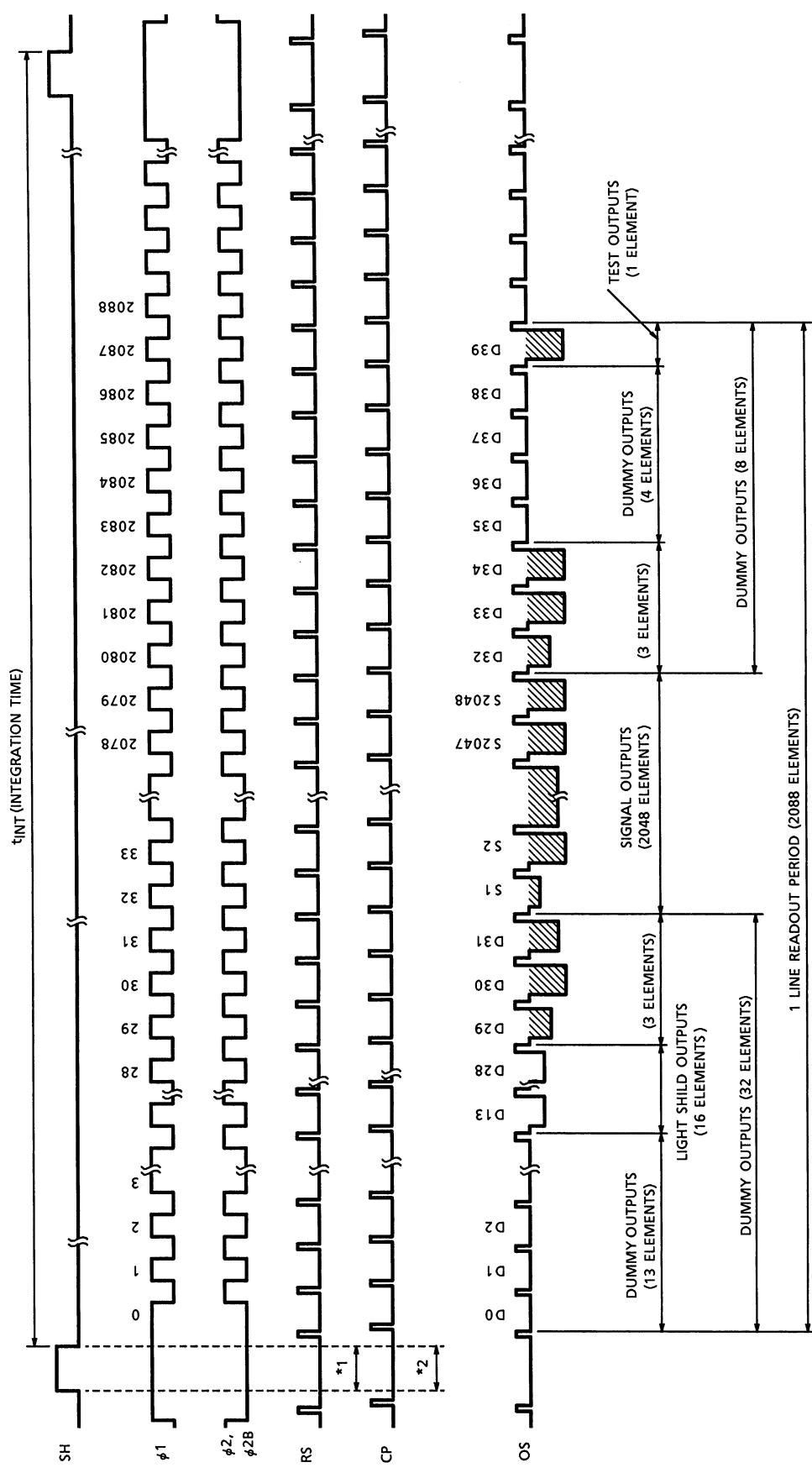
TIMING REQUIREMENTS

SH, φ1 Timing
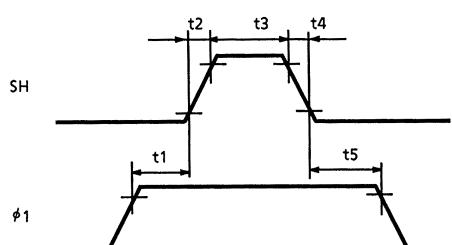
φ2, RS, CP, OS Timing
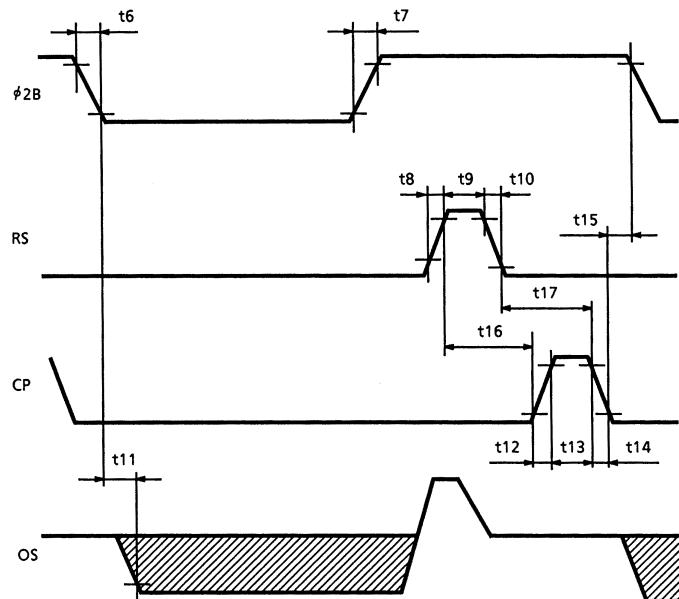
SH, RS, CP Timing
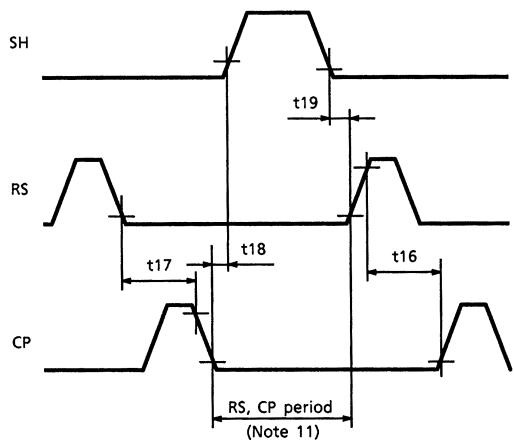
φ1, φ2 CROSS POINT
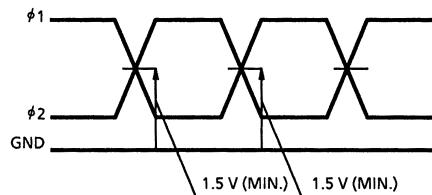
NOTE 11: Each RS and CP pins put to Low level during this period

CHARACTERISTIC	SYMBOL	MIN	TYP. (Note12)	MAX	UNIT
Pulse Timing of SH and φ1	t1, t5	200	500	—	ns
SH Pulse Rise Time, Fall Time	t2, t4	0	50	—	ns
SH Pulse Width	t3	1000	1500	—	ns
φ2B Pulse Rise Time, Fall Time	t6, t7	0	100	—	ns
RS Pulse Rise Time, Fall Time	t8, t10	0	20	—	ns
RS Pulse Width	t9	10	100	—	ns
Video Data Delay Time (Note 13)	t11	—	15	—	ns
CP Pulse Rise Time, Fall Time	t12, t14	0	20	—	ns
CP Pulse Width	t13	10	100	—	ns
Pulse Timing of φ2B and CP	t15	0	50	—	ns
Pulse Timing of RS and CP	t16	0	100	—	ns
	t17	10	100	—	
Pulse Timing of SH and CP	t18	200	—	—	ns
Pulse Timing of SH and RS	t19	200	—	—	ns

Note 12:   TYP. is the case of fRS = 1.0 MHz
Note 13:   Load Resistance is 100 kΩ

CAUTION

1. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

CCD Image Sensor is protected against static electricity, but interior puncture mode device due to static electricity is sometimes detected. In handing the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

a. Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.

b. Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.

c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.

It is not necessarily required to execute all precaution items for static electricity.

It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

Since this package is not strong against mechanical stress, you should not reform the lead frame.

We recommend to use a IC-inserter when you assemble to PCB.

5. Soldering

Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

Using a soldering iron, complete soldering within ten seconds for lead temperatures of up to 260°C, or within three seconds for lead temperatures of up to 350°C.

PACKAGE DIMESIONS

WDIP22-G-400-2.54A (A)

Unit : mm

9.09±0.8 (Note 1)   28.6(14μm×2048)

22   N   12

4.825±0.5

1   11

9.65±0.3

3.22±0.5

(Note 3)
0.7±0.1

10.16±0.25

0.25 +0.1 −0.05

41.6±0.5

(Note 2)
1.5±0.3

8.1 TYP   2.54±0.25   0.47±0.15

4.0±0.5
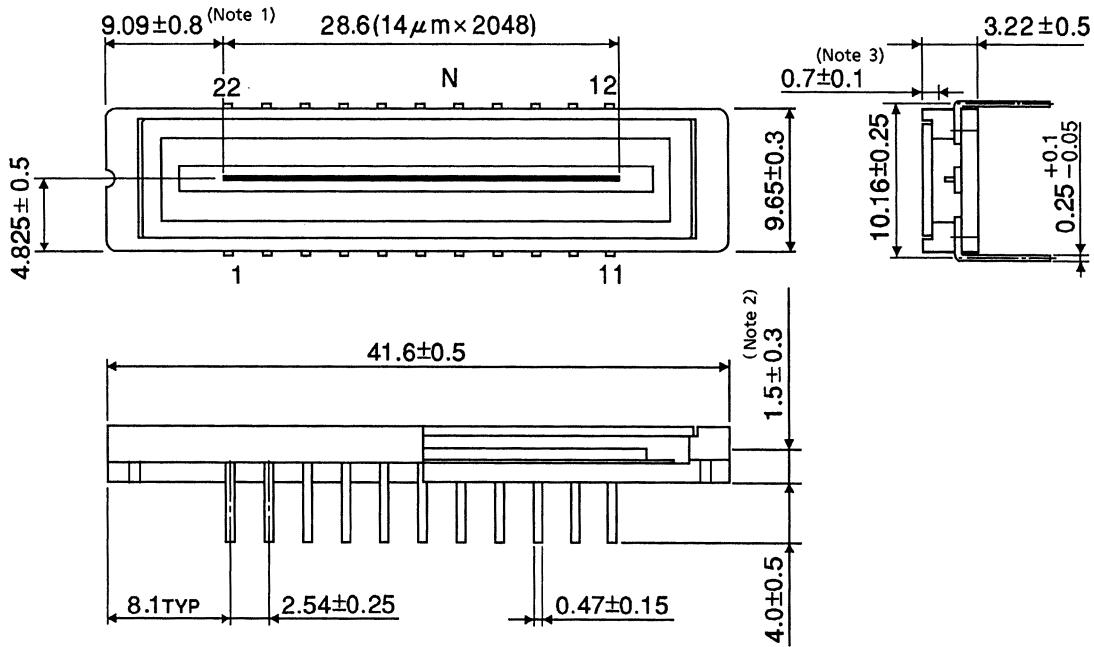
Note 1: No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.
Note 2: TOP OF CHIP TO BOTTOM OF PACKAGE.
Note 3: GLASS THICKNES (n = 1.5)

RESTRICTIONS ON PRODUCT USE

2004-02-09